ting this the most was a cross-section stron density  $n_s$  in pical values are  $n_s$  on of the ionized illity in the 2DEG e path larger than the scattering, and fistance between

top of the hetero pattern, one can ew Ref. 17). One (100 nm thick) is sensitive resist. tope) results in a e Fig. 1.3a). An in shown in Fig. istrate where the by dissolving the libstrate (see Fig. eam lithography

DEG. The "hard" of the 2DEG not on region, so the defined width. 18 eason the pattern is the electron gas gate geometry, as it-gate technique ohic width of the

FIG 1.2. (a) Cross-section of a GaAs/AlGaAs hetero structure with typical layer thicknesses. A negative voltage  $V_g$  applied to the metal split-gate confines the electrons laterally in the 2DEG. (b) Topview of a QPC. The dotted line indicates the depletion region in the 2DEG, which is tuned by  $V_g$ . The two wide 2DEG regions act as reservoirs, emitting electrons through the QPC with energies up to their electro chemical potentials  $\mu_1$  and  $\mu_2$ . A voltage difference V = $(\mu_1 - \mu_2)/e$  results in a net current I through the QPC.

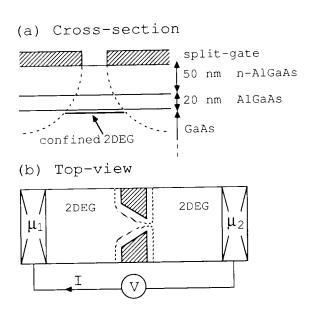
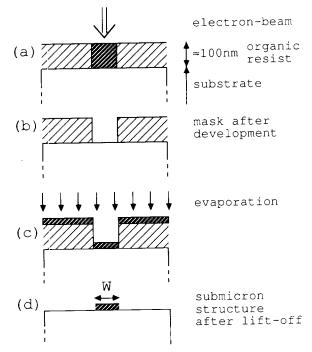


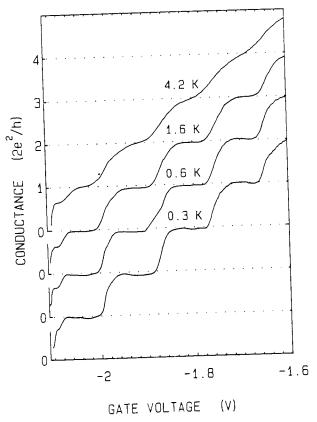
FIG. 1.3. Outline of the electronbeam lithography procedure for fabricating submicron structures.



and B = 0, f.22).

the thermal energy rsus gate voltage  $V_g$  as  $V_g$  is made more a pinched-off point 2/h. In total 16 steps  $V_g$  and pinch-off. This  $V_g$  the the three t

temperatures.<sup>25</sup> The hly linear at 4.2 K, in lassical result cannot 1.3.1 whenever  $\lambda_F/2$  (which is 21 nm was an estimate of the 5 than the lithographic



**FIG. 1.6.** Conductance versus gate voltage at B=0 and different temperatures. Increasing the temperature thermally averages the higher plateaus first (from Ref. 25).

width of 250 nm. These considerations are reminiscent of the states of a particle-in-a-1D-box, which, as we show below, is the basic idea behind the conductance quantization.

We note that the conductance quantization is not exact. First, a series resistance ( $\approx 400~\Omega$ ) originating from the wide 2DEG regions has been subtracted to line up the plateaus at their quantized values.<sup>22</sup> Furthermore, the plateaus are not completely flat. This may be due to scattering at impurities in the vicinity of the QPC or, as we discuss below, the abruptness of the constriction.

We now show that the conductance quantization results from transport through 1D subbands. To calculate transport through a QPC we start with the Hamiltonian: